

BC847DS

45 V, 100 mA NPN/NPN general-purpose transistor Rev. 01 — 25 August 2009 Produ

Product data sheet

1. Product profile

1.1 General description

NPN/NPN general-purpose transistor pair in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors
- AEC-Q101 qualified

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V_{CEO}	collector-emitter voltage	open base	-	-	45	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	200	300	450	



45 V, 100 mA NPN/NPN general-purpose transistor

2. Pinning information

Table 2. Pinning

Table 2.	Filling		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1	D. D. D.	
2	base TR1	<u> </u>	6 5 4
3	collector TR2	0	TR2
4	emitter TR2	<u> </u>	(TR1)
5	base TR2		
6	collector TR1		1 2 3
			sym020

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BC847DS	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4. Marking codes

Type number	Marking code
BC847DS	ZL

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	45	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	250	mW
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	380	mW

BC847DS Nexperia

45 V, 100 mA NPN/NPN general-purpose transistor

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		– 55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

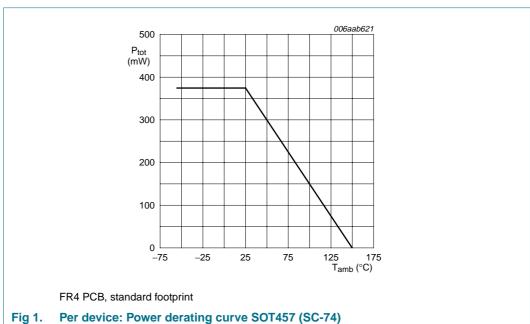


Fig 1.

Thermal characteristics 6.

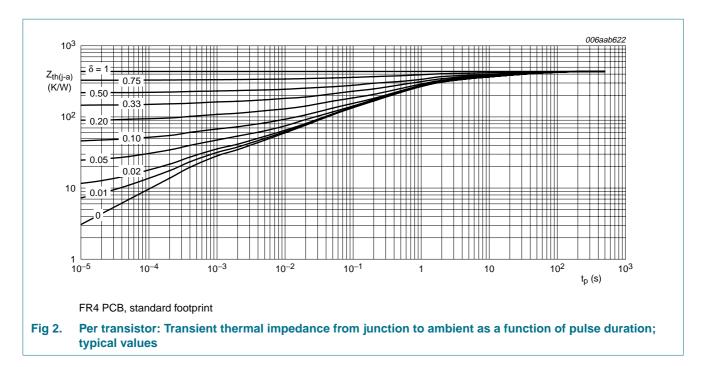
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	500	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	250	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	328	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

BC847DS © Nexperia B.V. 2009. All rights reserved.

45 V, 100 mA NPN/NPN general-purpose transistor



7. Characteristics

Table 7. Characteristics

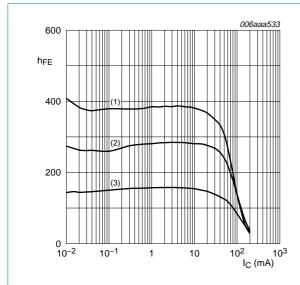
 T_{amb} = 25 °C unless otherwise specified.

· anno =		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$	-	-	15	nA
		$V_{CB} = 30 \text{ V; } I_E = 0 \text{ A;}$ $T_j = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; I_C = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 V$				
		$I_C = 10 \mu A$	-	280	-	
		$I_C = 2 \text{ mA}$	200	300	450	
V _{CEsat}	collector-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	55	100	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	-	200	300	mV
V_{BEsat}	base-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	755	850	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	-	1000	-	mV
V_{BE}	base-emitter voltage	V _{CE} = 5 V				
		$I_C = 2 \text{ mA}$	580	650	700	mV
		$I_C = 10 \text{ mA}$	-	-	770	mV

45 V, 100 mA NPN/NPN general-purpose transistor

Table 7. Characteristics ... continued $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

anno	<u>'</u>	•				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	1.9	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = i_c = 0 \text{ A};$ f = 1 MHz	-	11	-	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	100	-	-	MHz
NF noise figure	$V_{CE} = 5 \text{ V; } I_{C} = 0.2 \text{ mA;}$ $R_{S} = 2 \text{ k}\Omega;$ f = 10 Hz to 15.7 kHz	-	1.9	-	dB	
		$V_{CE} = 5 \text{ V; } I_{C} = 0.2 \text{ mA;}$ $R_{S} = 2 \text{ k}\Omega; f = 1 \text{ kHz;}$ B = 200 Hz	-	3.1	-	dB



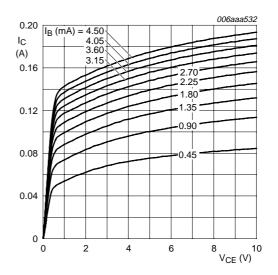
 $V_{CE} = 5 V$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. Per transistor: DC current gain as a function of collector current; typical values

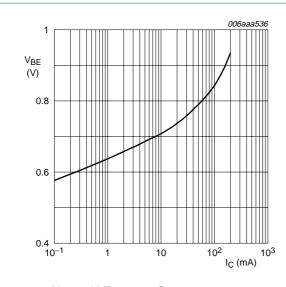


 $T_{amb} = 25 \, ^{\circ}C$

Fig 4. Per transistor: Collector current as a function of collector-emitter voltage; typical values

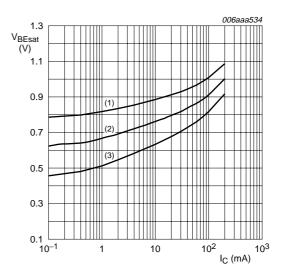
5 of 12

45 V, 100 mA NPN/NPN general-purpose transistor



 $V_{CE} = 5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$

Fig 5. Per transistor: Base-emitter voltage as a function of collector current; typical values



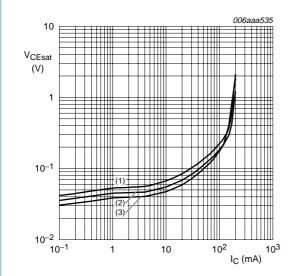
 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$

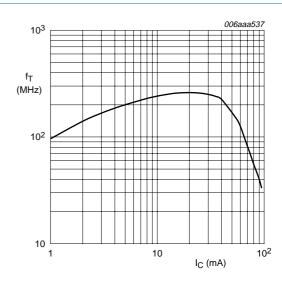
(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Product data sheet

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values



 $V_{CE} = 5 \text{ V}; T_{amb} = 25 \,^{\circ}\text{C}$

Fig 8. Per transistor: Transition frequency as a function of collector current; typical values

BC847DS © Nexperia

Rev. 01 — 25 August 2009

45 V, 100 mA NPN/NPN general-purpose transistor

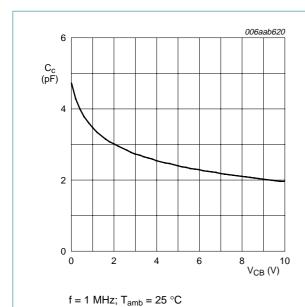


Fig 9. Per transistor: Collector capacitance as a function of collector-base voltage; typical values

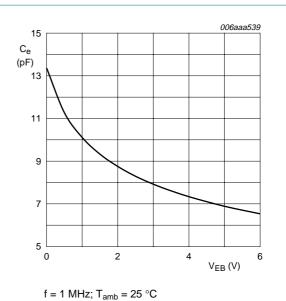


Fig 10. Per transistor: Emitter capacitance as a function of emitter-base voltage; typical values

© Nexperia B.V. 2009. All rights reserved.

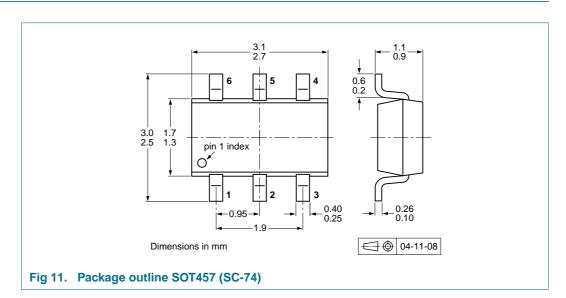
45 V, 100 mA NPN/NPN general-purpose transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

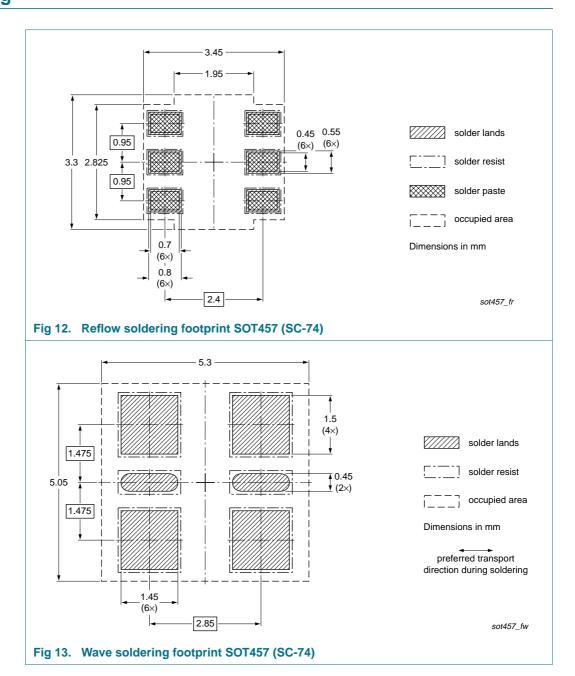


10. Packing information

Please refer to packing information on http://www.nexperia.com.

45 V, 100 mA NPN/NPN general-purpose transistor

11. Soldering



45 V, 100 mA NPN/NPN general-purpose transistor

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC847DS	20090825	Product data sheet	-	-

45 V, 100 mA NPN/NPN general-purpose transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

13.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by Nexperia. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

© Nexperia B.V. 2009. All rights reserved.

14. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data
2	Pinning information 2
3	Ordering information
4	Marking 2
5	Limiting values
6	Thermal characteristics 3
7	Characteristics4
8	Test information
8.1	Quality information
9	Package outline 8
10	Packing information 8
11	Soldering 9
12	Revision history
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks11
14	Contents 12

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

45 V, 100 mA NPN/NPN general-purpose transistor

All rights reserved.

Date of release: 25 August 2009 Document identifier: BC847DS